## BDW23/A/B/C

### **Hammer Drivers, Audio Amplifiers Applications**

- Power Darlington TR
  Complement to BDW24, BDW24A, BDW24B and BDW24C respectively



1.Base 2.Collector 3.Emitter

## **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

| Symbol           | Parameter                                    | Value      | Units |
|------------------|--|------------|-------|
| V <sub>CBO</sub> | Collector-Base Voltage                       |            |       |
|                  | : BDW23                                      | 45         | V     |
|                  | : BDW23A                                     | 60         | V     |
|                  | : BDW23B                                     | 80         | V     |
|                  | : BDW23C                                     | 100        | V     |
| $V_{CEO}$        | Collector-Emitter Voltage                    |            |       |
|                  | : BDW23                                      | 45         | V     |
|                  | : BDW23A                                     | 60         | V     |
|                  | : BDW23B                                     | 80         | V     |
|                  | : BDW23C                                     | 100        | V     |
| V <sub>EBO</sub> | Emitter-Base Voltage                         | 5          | V     |
| I <sub>C</sub>   | Collector Current (DC)                       | 6          | Α     |
| I <sub>CP</sub>  | *Collector Current (Pulse)                   | 8          | Α     |
| I <sub>B</sub>   | Base Current                                 | 0.2        | Α     |
| P <sub>C</sub>   | Collector Dissipation (T <sub>C</sub> =25°C) | 50         | W     |
| T <sub>J</sub>   | Junction Temperature                         | 150        | °C    |
| T <sub>STG</sub> | Storage Temperature                          | - 65 ~ 150 | °C    |

| Electrical | Characteristics  | T <sub>C</sub> =25°C unless otherwise noted |
|------------|------------------|---|
| Electrical | Character istics | I ~=25°C unless otherwise noted             |

| Symbol                              | Parameter   | Test Condition   | Min.                  | Тур. | Max.                     | Unit<br>s            |
|-------------------------------------|---|--|-----------------------|------|--------------------------|----------------------|
| V <sub>CEO</sub> (sus)              | Collector-Emitter Sustaining Voltage : BDW23 : BDW23A : BDW23B : BDW23C | I <sub>C</sub> = 100mA, I <sub>B</sub> = 0   | 45<br>60<br>80<br>100 |      |                          | V<br>V<br>V          |
| I <sub>CBO</sub>                    | Collector Cut-off Current : BDW23 : BDW23A : BDW23B : BDW23C            | $V_{CB} = 45V, I_{E} = 0$ $V_{CB} = 60V, I_{E} = 0$ $V_{CB} = 80V, I_{E} = 0$ $V_{CB} = 100V, I_{E} = 0$   |                       |      | 200<br>200<br>200<br>200 | μΑ<br>μΑ<br>μΑ<br>μΑ |
| I <sub>CEO</sub>                    | Collector Cut-off Current : BDW23 : BDW23A : BDW23B : BDW23C            | V <sub>CE</sub> = 22V, I <sub>B</sub> = 0<br>V <sub>CE</sub> = 30V, I <sub>B</sub> = 0<br>V <sub>CE</sub> = 40V, I <sub>B</sub> = 0<br>V <sub>CE</sub> = 50V, I <sub>B</sub> = 0 |                       |      | 500<br>500<br>500<br>500 | μΑ<br>μΑ<br>μΑ<br>μΑ |
| I <sub>EBO</sub><br>h <sub>FE</sub> | Emitter Cut-off Current * DC Current Gain                               | $V_{EB} = 5V, I_{C} = 0$ $V_{CE} = 3V, I_{C} = 1A$ $V_{CE} = 3V, I_{C} = 2A$   | 1000<br>750           |      | 2 20000                  | mA                   |
| V <sub>CE</sub> (sat)               | * Collector-Emitter Saturation Voltage                                  | $V_{CE} = 3V, I_{C} = 6A$ $I_{C} = 2A, I_{B} = 8mA$ $I_{C} = 6A, I_{B} = 60mA$   | 100                   |      | 2 3                      | V                    |
| V <sub>BE</sub> (sat)               | * Base-Emitter Saturation Voltage                                       | $I_{C} = 2A, I_{B} = 8mA$  |                       |      | 2.5                      | V                    |
| V <sub>BE</sub> (on)                | * Base-Emitter ON Voltage   | $V_{CE} = 3V, I_{C} = 1A$<br>$V_{CE} = 3V, I_{C} = 6A$   |                       |      | 2.5<br>3                 | V<br>V               |
| V <sub>F</sub>                      | * Parallel Diode Forward Voltage  | I <sub>F</sub> = 2A  |                       |      | 1.8                      | V                    |

<sup>\*</sup> Pulse Test: PW =300μs, duty Cycle =1.5% Pulsed

# **Typical Characteristics**

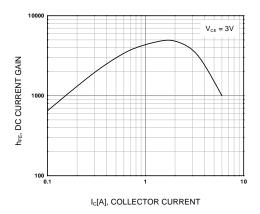


Figure 1. DC current Gain

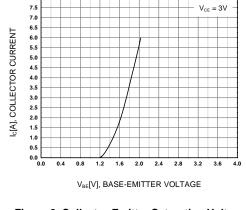


Figure 2. Collector-Emitter Saturation Voltage

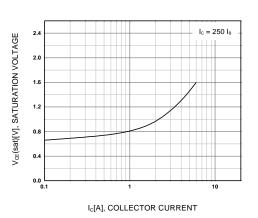


Figure 3. Base-Emitter On Voltage

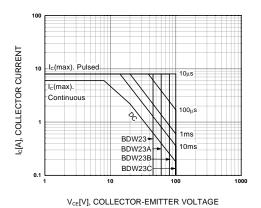


Figure 4. Safe Operating Area

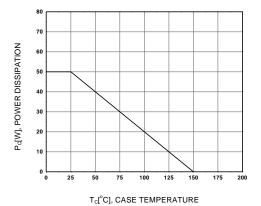
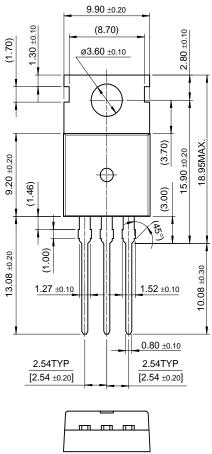
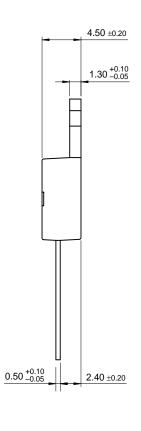


Figure 5. Power Derating

## **Package Demensions**

TO-220





10.00 ±0.20

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